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(54) SEMICONDUCTOR MEMORY DEVICE

(57) Abstract:

PROBLEM TO BE SOLVED: To prevent data in a memory cell from being broken down so as to enhance its reliability in a semiconductor memory device which requires an I/O mask operation in a block write operation.

SOLUTION: In an I/O mask operation in a block write operation, a change in the precharging level of a common data line is suppressed so as to prevent data in a memory cell from being broken down, and, in addition, it is required to stabilize the level. In order to suppress a change in the precharging level of the common data line to a power-supply level -VTN or higher, a precharging part (a) is provided with MOST's 13, 14. Consequently, MOST's 8, 9 precharge respective P-data lines to a power-supply voltage level by means of a precharging control signal ϕP. The NMOST's 13, 14 precharge the data lines to a voltage level in which threshold voltage portions of the NMOST's 13, 14 are subtracted from the power-supply voltage level, while the inverted signal of the prechariging control signal ϕP is used.